

**Silicon PNP Power Transistors**

**2SB1135**

**DESCRIPTION**

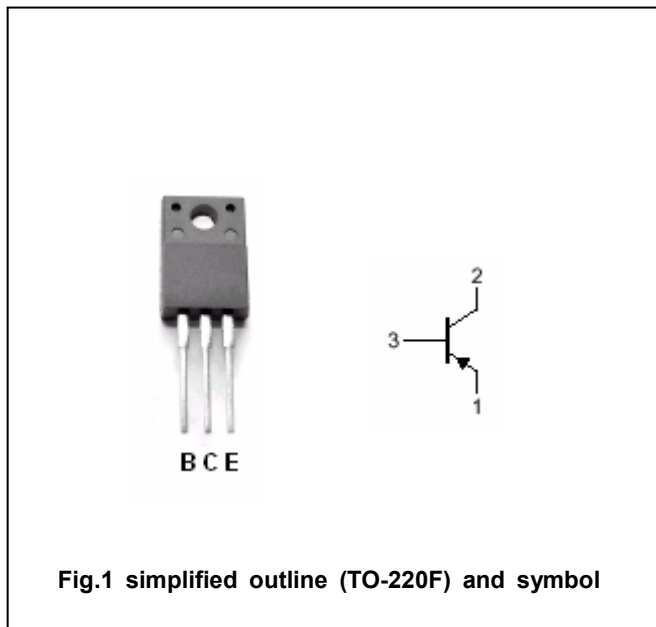
- With TO-220F package
- Complement to type 2SD1668
- Low collector saturation voltage
- Wide ASO

**APPLICATIONS**

- Relay drivers
- High speed inverters;converters
- General high current switching application

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-7	A
I <sub>CM</sub>	Collector current-peak		-12	A
I <sub>B</sub>	Base current		-0.5	A
P <sub>C</sub>	Collector dissipation	T <sub>a</sub> =25°C	2	W
		T <sub>C</sub> =25°C	30	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-1mA ; R <sub>BE</sub> =∞	-50			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA ; I <sub>E</sub> =0	-60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A; I <sub>B</sub> =-0.4A			-0.4	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-40V ; I <sub>E</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-100	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V	70		280	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-2V	30			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V		10		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-2.0A I <sub>B1</sub> =-I <sub>B2</sub> =-0.2A		0.2		μs
t <sub>s</sub>	Storage time			0.7		μs
t <sub>f</sub>	Fall time			0.1		μs

◆ h<sub>FE-1</sub> Classifications

Q	R	S
70-140	100-200	140-280

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PACKAGE OUTLINE

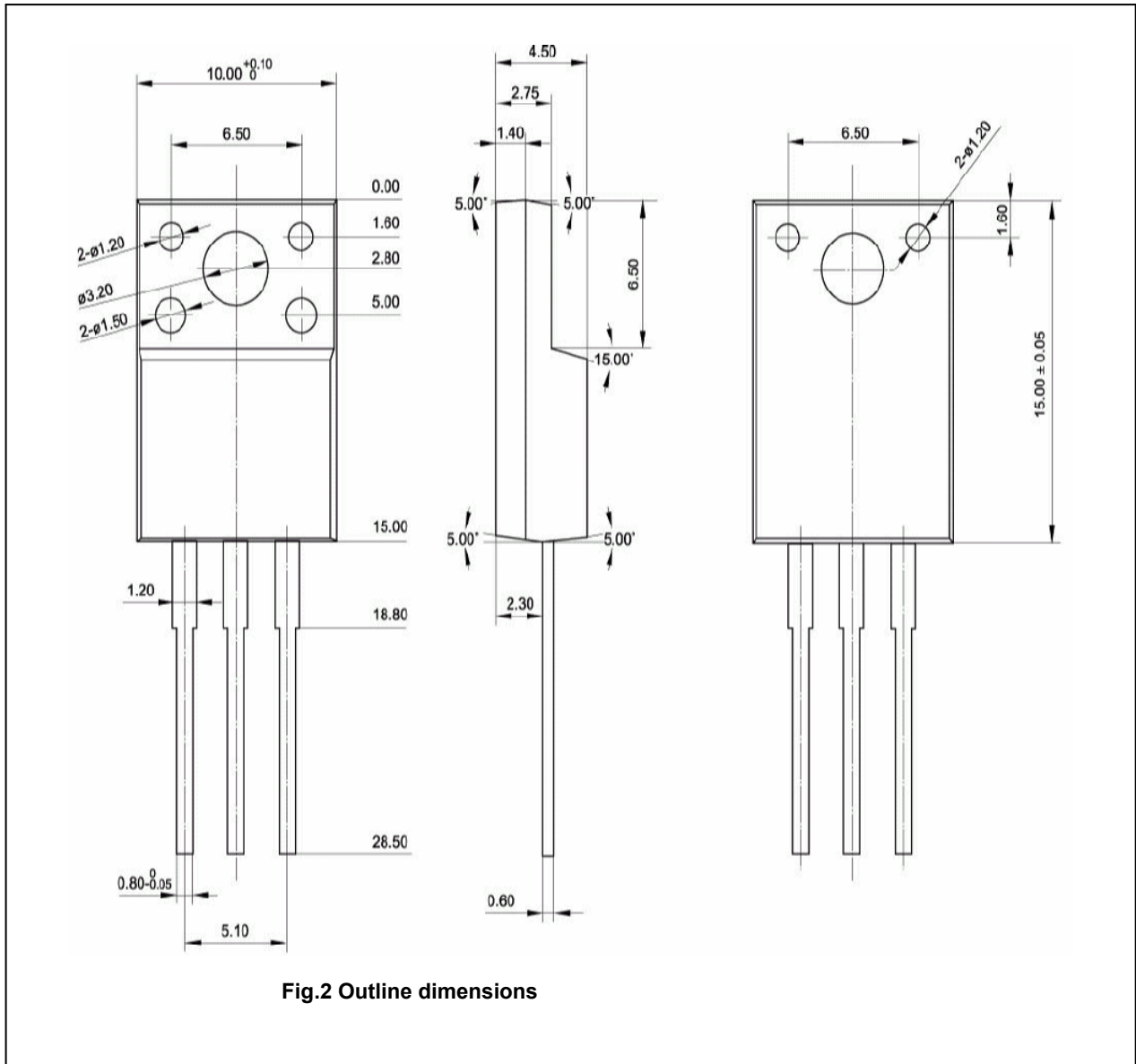


Fig.2 Outline dimensions

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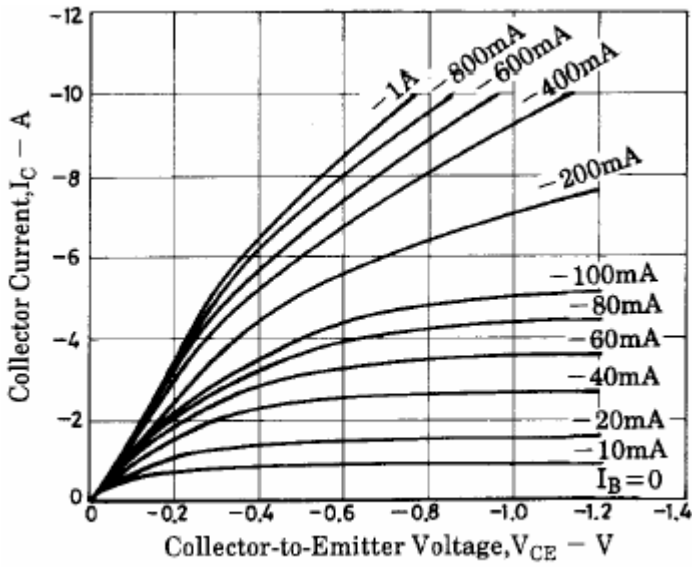


Fig.3 Static Characteristic

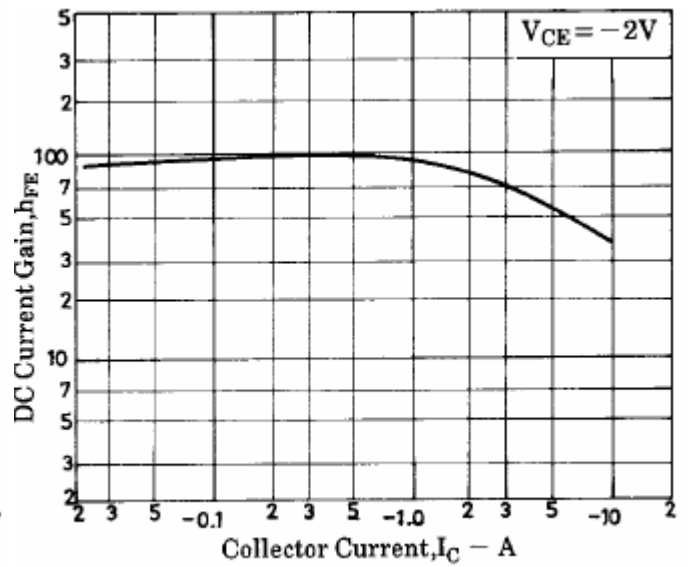


Fig.4 DC current Gain

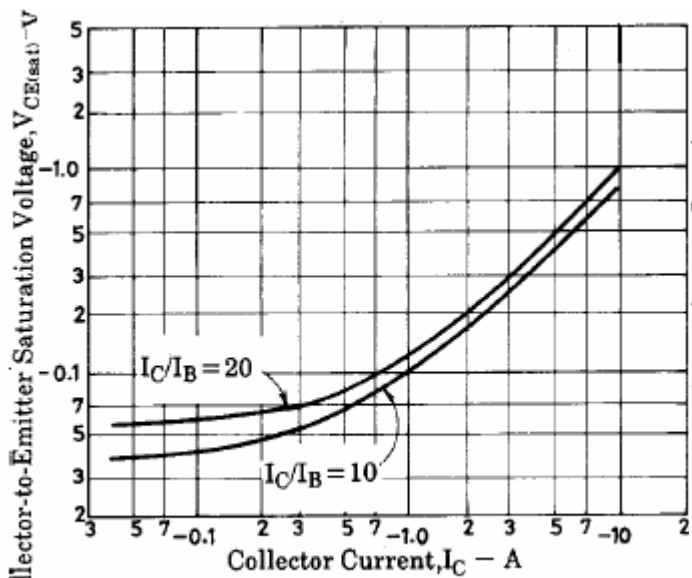


Fig.5 Collector-Emitter Saturation Voltage

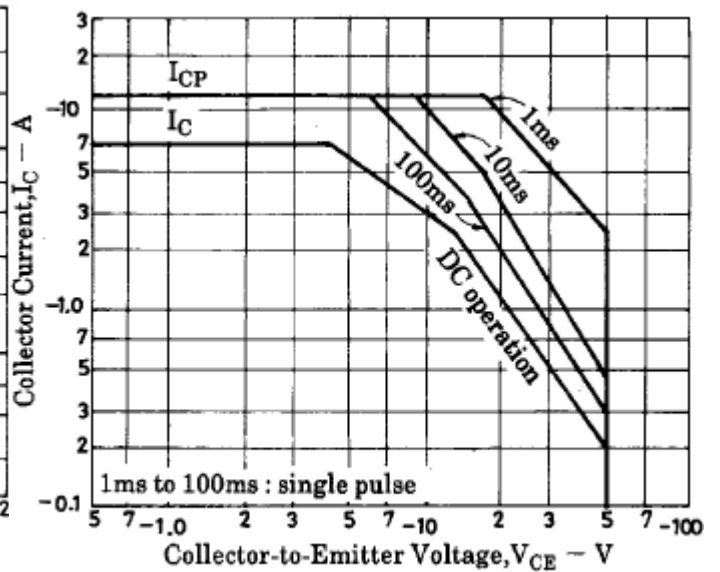


Fig.6 Safe Operating Area